

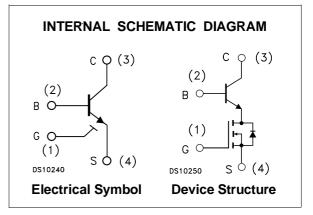
STC20DE90

900 V - 20 A - 60 m Ω ESBT

ADVANCE DATA

- HIGH VOLTAGE / HIGH CURRENT CASCODE CONFIGURATION
- LOW EQUIVALENT ON RESISTANCE
- VERY FAST-SWITCH UP TO 150 KHz
- SQUARED RBSOA UP TO 900 V
- ULTRA LOW Ciss
- LOW DYNAMIC VCS(ON)

TO-247 4 Leads



ABSOLUTE MAXIMUM RATINGS

Symbol	Parameter	Value	Unit
V _{CS(SS)}	Collector-Source Voltage (V _{BS} =V _{GS} = 0V)	900	V
V _{BS(OS)}	Base-SourceVoltage ($I_C = 0, V_{GS} = 0V$)	30	V
V _{SB(OS)}	Source-Base Voltage ($I_C = 0, V_{GS} = 0V$)	10	V
V _{GS}	Gate-Source Voltage	± 20	V
Ι _C	Collector Current	20	Α
Ісм	Collector Peak Current (t _p ≤ 5 ms)	60	Α
Ι _Β	Base Current	4	Α
I _{BM}	Base Peak Current (t _p ≤ 1 ms)	20	Α
P _{tot}	Total Dissipation at $T_c = 25 \ ^{\circ}C$	tbd	W
T _{stg}	Storage Temperature	-65 to 150	°C
Tj	Max. Operating Junction Temperature	150	°C

THERMAL DATA

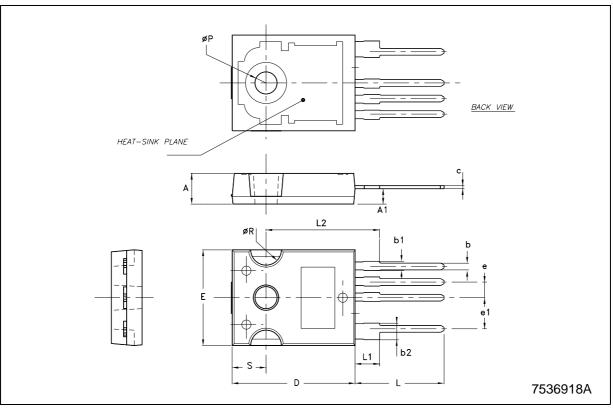
R _{thj-case}	Thermal	Resistance	Junction-Case	Max	tbd	°C/W
R _{thc-h}	Thermal	Resistance	Case-heatsink Wi	th Conductive Grease		
	Applied			Max	tbd	°C/W

ELECTRICAL CHARACTERISTICS ($T_{case} = 25 \ ^{\circ}C$ unless otherwise specified)

Symbol	Parameter	Test Conditions	Min.	Тур.	Max.	Unit
I _{CS(SS)}	Collector-Source Current (V _{BS} = V _{GS} =0 V)	V _{CS(SS)} = 900 V			100	μA
$I_{BS(OS)}$	Base-Source Current (I _C = 0, V _{GS} =0 V)	$V_{BS(OS)} = 30 V$			10	μA
$I_{SB(OS)}$	Source-Base Current (I _C = 0, V _{GS} =0 V)	$V_{SB(OS)} = 10 V$			100	μA
I _{GS(S)}	Gate-Source Leakage (V _{BS} = 0 V)	$V_{GS} = \pm 20 V$			100	nA
$V_{CS(ON)}$	Collector-Source ON Voltage			1	1.4	V
R _{CS(ON)}	Equivalent ON Resistance	$V_{GS} = 10 \text{ V} \qquad I_C = 15 \text{ A}$ $I_B = 3 \text{ A}$		60	75	mΩ
h _{FE}	DC Current Gain	$I_{C} = 15 \text{ A } V_{CS} = 1 \text{ V } V_{GS} = 10 \text{ V}$	6	9	12	
V _{BS(ON)}	Base-Source ON Voltage	$I_{C} = 15 \text{ A} \qquad I_{B} = 3 \text{ A}$ $V_{GS} = 10 \text{ V}$		1.4	1.8	V
$V_{GS(th)}$	Gate Threshold Voltage	$V_{BS} = V_{GS}$ $I_B = 250 \ \mu A$	1	1.7	2.5	V
Ciss	Input Capacitance	tbd	tbd	tbd	tbd	pF
Q _{GS}	Gate-Source Charge	tbd	tbd	tbd	tbd	nC
t _s t _f	INDUCTIVE LOAD Storage Time Fall Time	tbd	tbd tbd	tbd tbd	tbd tbd	μs ns
t _{d(on)}	INDUCTIVE LOAD Time Delay Turn-on	tbd	tbd	tbd	tbd	ns
t _{r(on)}	INDUCTIVE LOAD Time Rise Turn-off	tbd	tbd	tbd	tbd	ns
$V_{\text{CS}(\text{dyn})}$	Collector-Source Dynamic Voltage	tbd	tbd	tbd	tbd	V
V _{CSW}	Maximum Collector Source Voltage without Snubber	tbd	tbd	tbd	tbd	V

TO-247 4 Leads	MECHANICAL DATA
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DIM.	mm				
Divi.	MIN.	TYP.	MAX.		
A	4.85		5.15		
A1	2.20		2.60		
b	0.95	1.10	1.30		
b1	1.30		1.70		
b2	2.50		2.90		
С	0.40		0.80		
D	19.85		20.15		
E	15.45		15.75		
е		2.54			
e1		5.08			
L	14.20		14.80		
L1	3.70		4.30		
L2		18.50			
ØP	3.55		3.65		
ØR	4.50		5.50		



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